



IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





BUJ103A

Silicon diffused power transistor

Rev. 4 — 8 November 2011

Product data sheet

1. Product profile

1.1 General description

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT78 (TO-220AB) plastic package.

1.2 Features and benefits

- Low thermal resistance
- Fast switching

1.3 Applications

- Electronic lighting ballasts
- DC-to-DC converters
- Inverters
- Motor control systems

1.4 Quick reference data

- $V_{CESM} \leq 700$ V
- $I_C \leq 4$ A
- $P_{tot} \leq 80$ W
- $h_{FEsat} = 12.5$ (typ)

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	base	<p>SOT78 (TO-220AB)</p>	<p>sym056</p>
2	collector		
3	emitter		
mb	mounting base; connected to collector		



3. Ordering information

Table 2. Ordering information

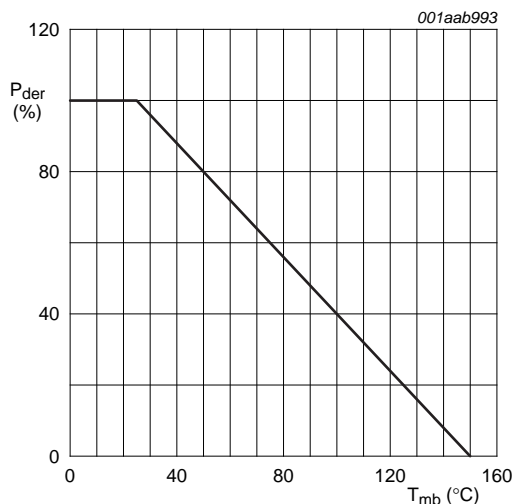
Type number	Package		Version
	Name	Description	
BUJ103A	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-leads	SOT78

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	peak collector-emitter voltage	$V_{BE} = 0\text{ V}$	-	700	V
V_{CBO}	collector-base voltage	open emitter	-	700	V
V_{CEO}	collector-emitter voltage	open base	-	400	V
I_C	collector current (DC)		-	4	A
I_{CM}	peak collector current		-	8	A
I_B	base current (DC)		-	2	A
I_{BM}	peak base current		-	4	A
P_{tot}	total power dissipation	$T_{mb} \leq 25\text{ °C}$; see Figure 1	-	80	W
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	150	°C



$$P_{der}(\%) = \frac{P_{tot}}{P_{tot(25\text{ °C})}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 2	-	-	1.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

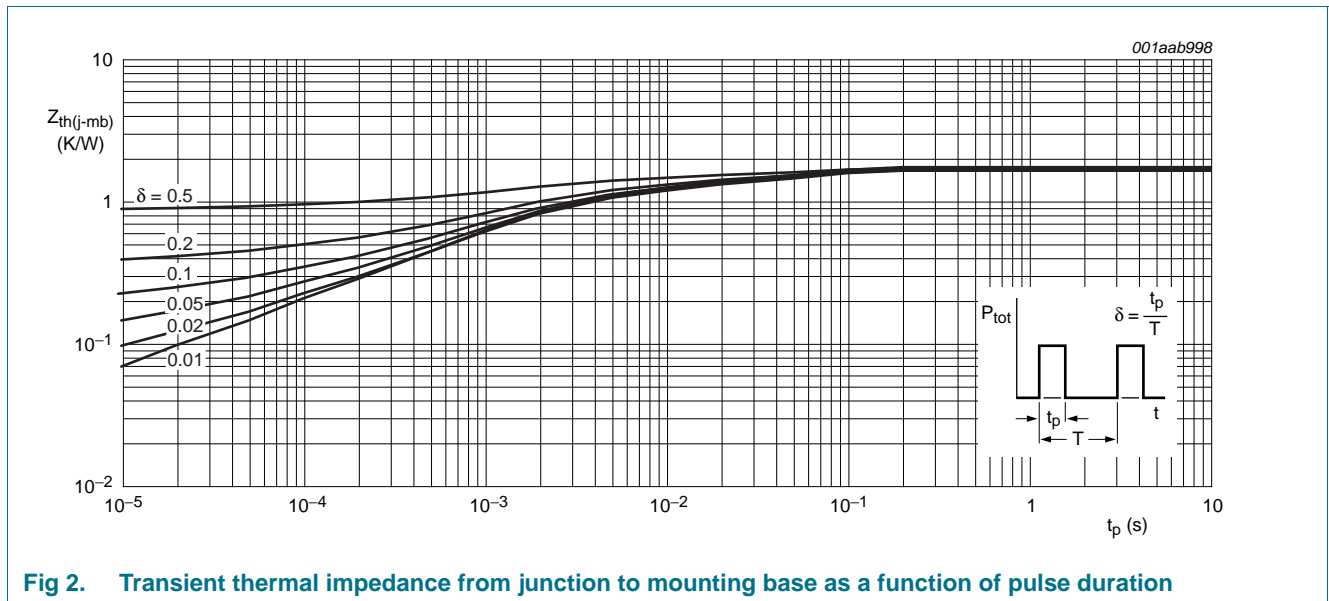


Fig 2. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 5. Characteristics

$T_{mb} = 25\text{ °C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{CES}	collector-emitter cut-off current	$V_{BE} = 0\text{ V}$; $V_{CE} = V_{CESMmax}$	[1]	-	1	mA
		$V_{BE} = 0\text{ V}$; $V_{CE} = V_{CESMmax}$; $T_j = 125\text{ °C}$	[1]	-	2	mA
I_{CBO}	collector-base cut-off current	$V_{BE} = 0\text{ V}$; $V_{CE} = V_{CESMmax}$	[1]	-	1	mA
I_{CEO}	collector-emitter cut-off current	$V_{CEO} = V_{CEOMmax} = 400\text{ V}$	[1]	-	0.1	mA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 7\text{ V}$; $I_C = 0\text{ A}$	-	-	0.1	mA
V_{CEOsus}	collector-emitter sustaining voltage	$I_B = 0\text{ A}$; $I_C = 10\text{ mA}$; $L = 25\text{ mH}$; see Figure 3 and 4	400	-	-	V
V_{CEsat}	collector-emitter saturation voltage	$I_C = 3.0\text{ A}$; $I_B = 0.6\text{ A}$; see Figure 10	-	0.25	1	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 3.0\text{ A}$; $I_B = 0.6\text{ A}$; see Figure 11	-	0.97	1.5	V
h_{FE}	DC current gain	$I_C = 1\text{ mA}$; $V_{CE} = 5\text{ V}$; see Figure 9	10	17	32	
		$I_C = 500\text{ mA}$; $V_{CE} = 5\text{ V}$	13	22	32	
h_{FEsat}	DC saturation current gain	$I_C = 2.0\text{ A}$; $V_{CE} = 5\text{ V}$	11	16	22	
		$I_C = 3.0\text{ A}$; $V_{CE} = 5\text{ V}$	-	12.5	-	
Dynamic characteristics						
Switching times (resistive load); see Figure 5 and 6						
t_{on}	turn-on time	$I_{Con} = 2.5\text{ A}$; $I_{Bon} = -I_{Boff} = 0.5\text{ A}$; $R_L = 75\text{ }\Omega$	-	0.52	0.6	μs
t_{stg}	storage time		-	2.7	3.3	μs
t_f	fall time		-	0.3	0.35	μs
Switching times (inductive load); see Figure 7 and 8						
t_{stg}	storage time	$I_{Con} = 2\text{ A}$; $I_{Bon} = 0.4\text{ A}$; $L_B = 1\text{ }\mu\text{H}$; $V_{BB} = -5\text{ V}$	-	1.2	1.4	μs
t_f	fall time		-	30	60	ns
Switching times (inductive load); see Figure 7 and 8						
t_{stg}	storage time	$I_{Con} = 2\text{ A}$; $I_{Bon} = 0.4\text{ A}$; $L_B = 1\text{ }\mu\text{H}$; $V_{BB} = -5\text{ V}$; $T_j = 100\text{ °C}$	-	-	1.8	μs
t_f	fall time		-	-	120	ns

[1] Measured with half sine-wave voltage (curve tracer).

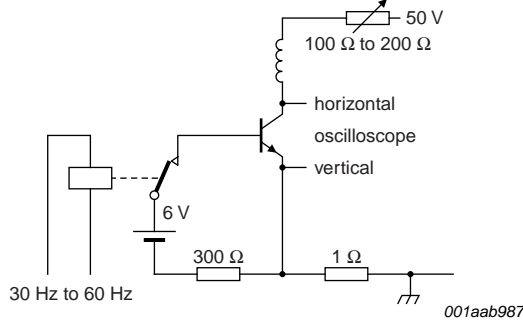


Fig 3. Test circuit for collector-emitter sustaining voltage

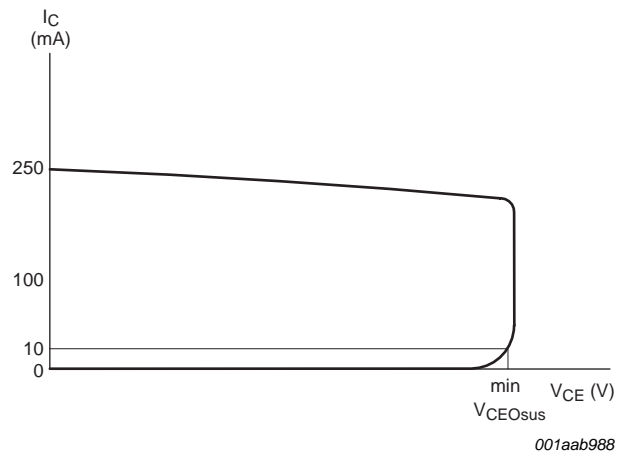
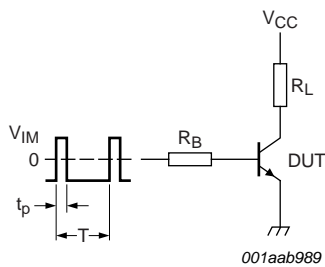


Fig 4. Oscilloscope display for collector-emitter sustaining voltage test waveform



$V_{IM} = -6\text{ V to }+8\text{ V}$; $V_{CC} = 250\text{ V}$; $t_p = 20\text{ }\mu\text{s}$;
 $\delta = t_p/T = 0.01$.
 R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig 5. Test circuit for resistive load switching

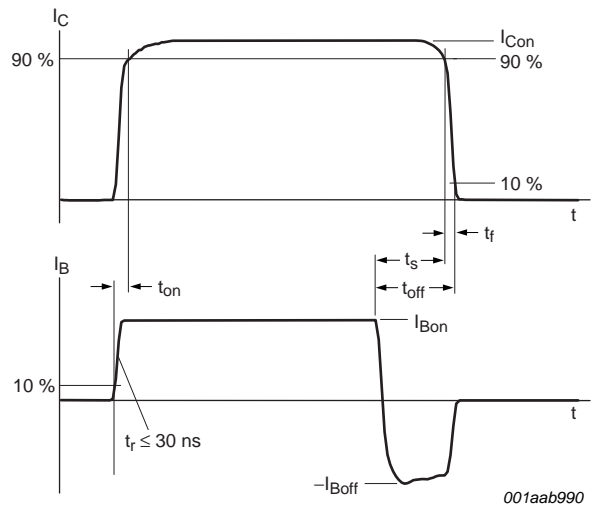
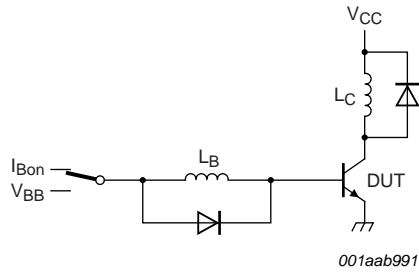


Fig 6. Switching times waveforms for resistive load



$V_{CC} = 300\text{ V}$; $V_{BB} = -5\text{ V}$; $L_C = 200\ \mu\text{H}$; $L_B = 1\ \mu\text{H}$.

Fig 7. Test circuit for inductive load switching

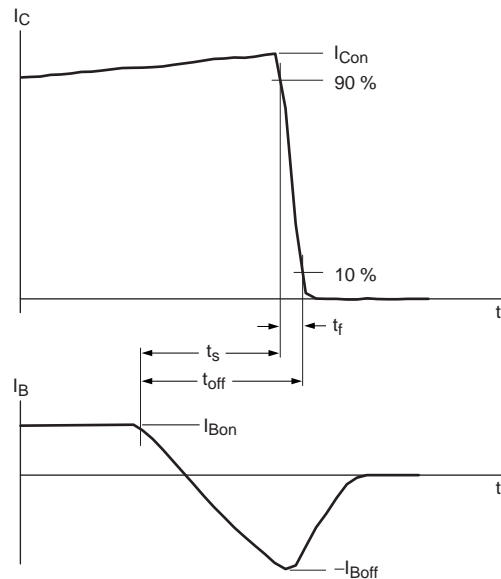


Fig 8. Switching times waveforms for inductive load

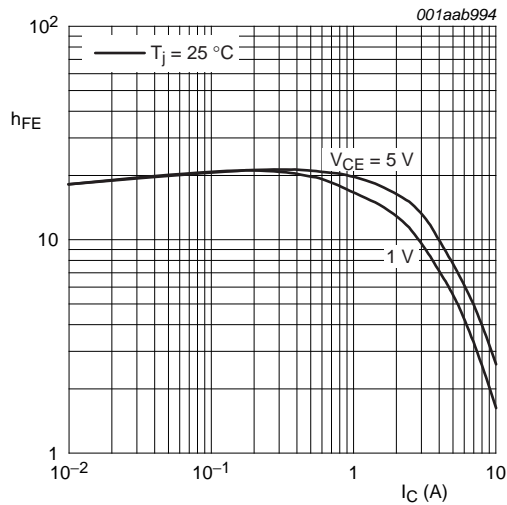
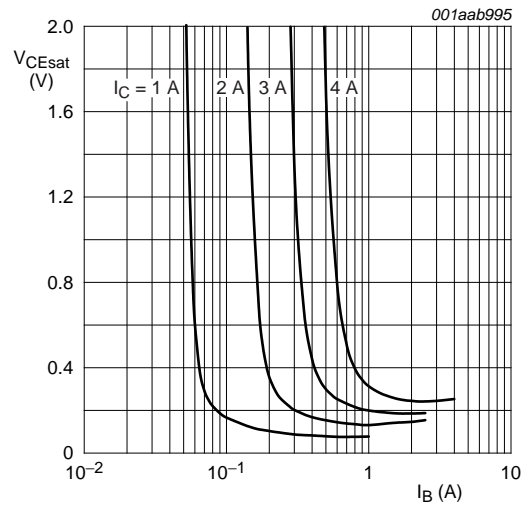
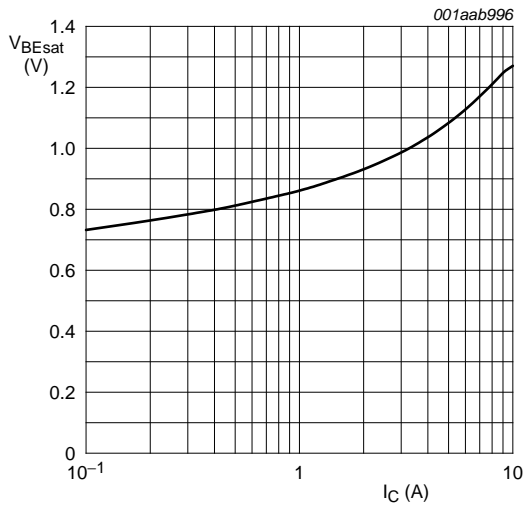


Fig 9. DC current gain as a function of collector current; typical values



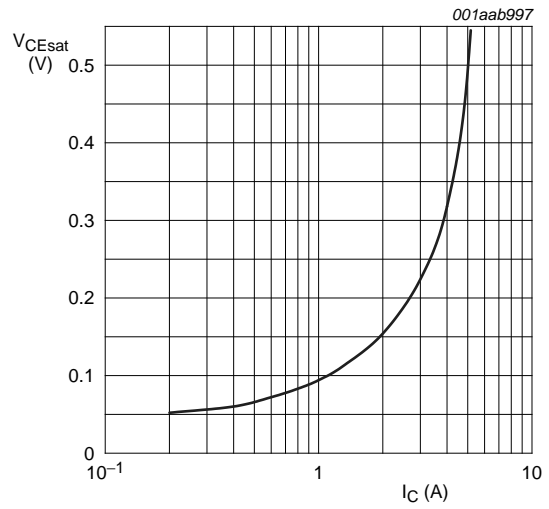
$T_j = 25\text{ }^\circ\text{C}$.

Fig 10. Collector-emitter saturation voltage as a function of base current; typical values



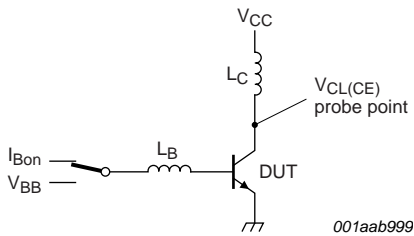
$I_C/I_B = 4$.

Fig 11. Base-emitter saturation voltage as a function of collector current; typical values



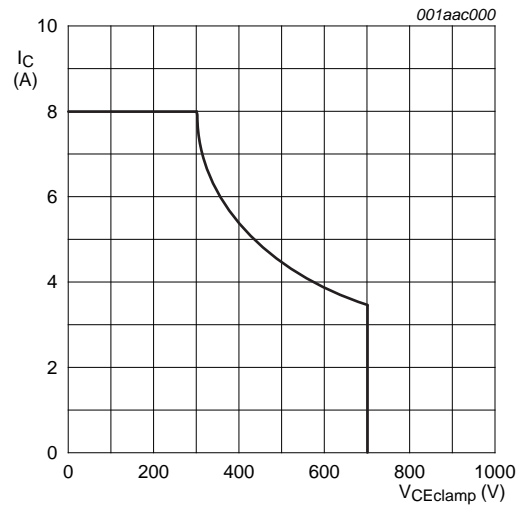
$I_C/I_B = 4$.

Fig 12. Collector-emitter saturation voltage as a function of collector current; typical values



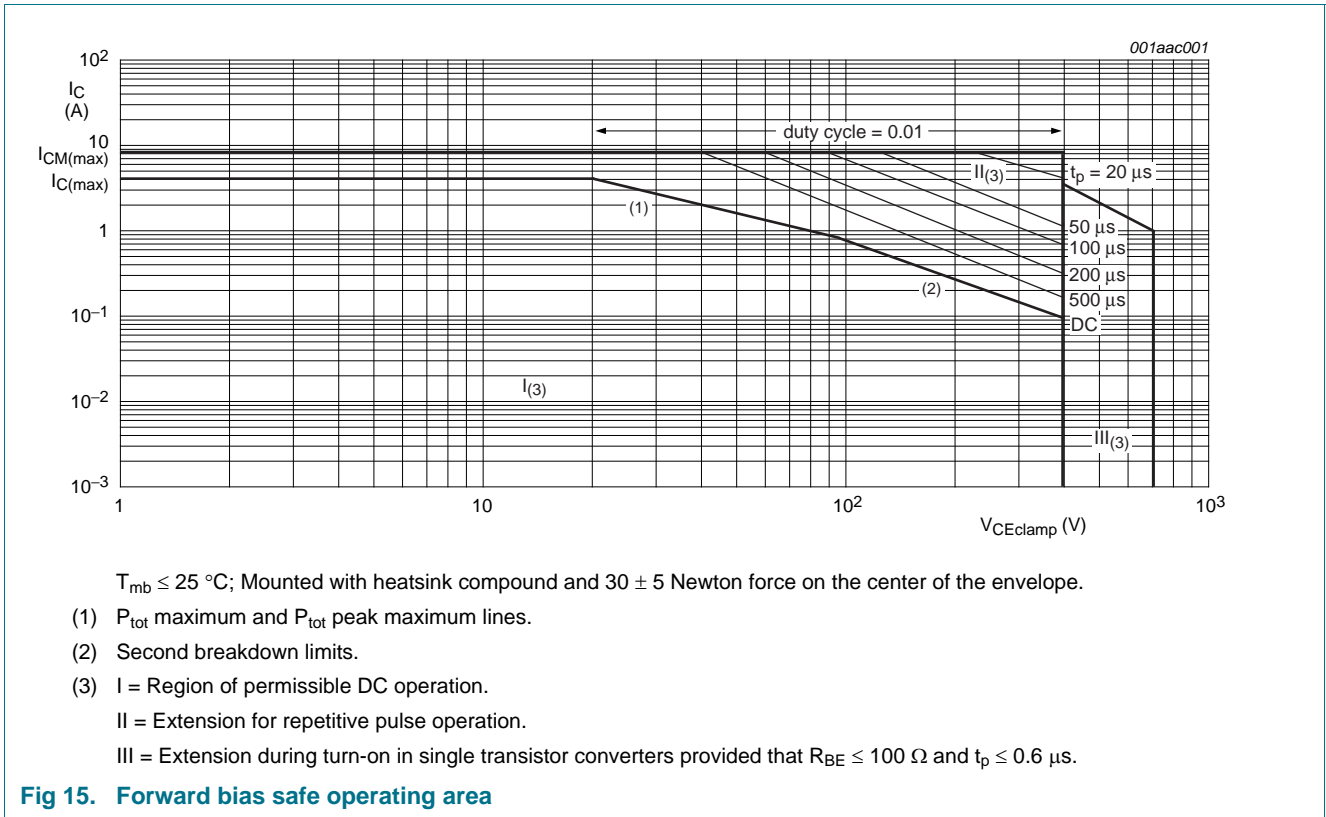
$V_{CEclamp} \leq 1000$ V; $V_{CC} = 150$ V; $V_{BB} = -5$ V; $L_B = 1$ μ H; $L_C = 200$ μ H.

Fig 13. Test circuit for reverse bias safe operating area



$T_j \leq T_{j(max)}$.

Fig 14. Reverse bias safe operating area



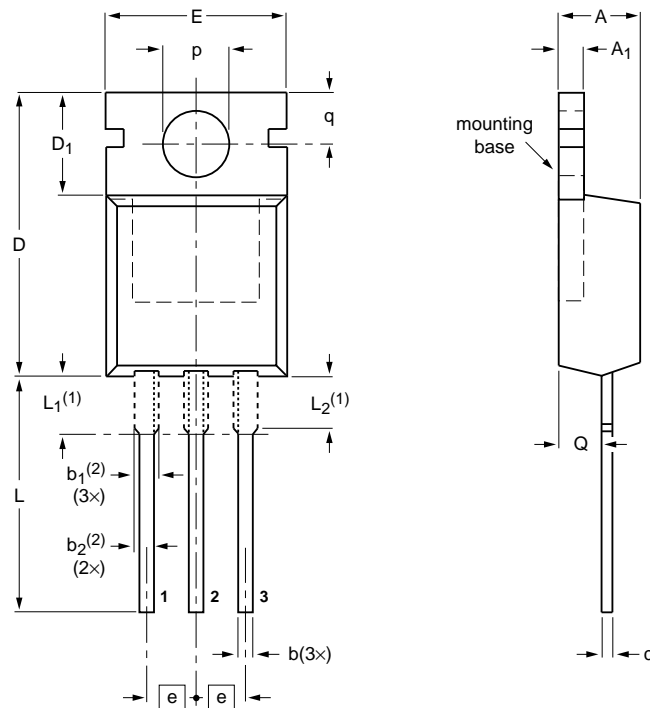
7. Package information

Epoxy meets requirements of UL94 V-0 at $\frac{1}{8}$ inch.

8. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (²)	b ₂ (²)	c	D	D ₁	E	e	L	L ₁ (¹)	L ₂ (¹) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig 16. Package outline SOT78 (TO-220AB)

9. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUJ103A v.4	20111108	Product data sheet	-	BUJ103A v.3
Modifications:		<ul style="list-style-type: none">• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.• Legal texts have been adapted to the new company name where appropriate.		
BUJ103A v.3	20050303	Product data sheet	-	BUJ103A_HG v.2
BUJ103A_HG v.2	19980918	Product data sheet	-	BUJ103A v.1
BUJ103A v.1	19980801	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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